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Contact us

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

4K Microwire Compatible Serial EEPROM

Device Selection Table

Part Number	Vcc Range	ORG Pin	Word Size	Temp Ranges	Packages
93AA66A	1.8-5.5	No	8-bit	I	P, SN, ST, MS, OT, MC, MN
93AA66B	1.8-5-5	No	16-bit	I	P, SN, ST, MS, OT, MC, MN
93LC66A	2.5-5.5	No	8-bit	I, E	P, SN, ST, MS, OT, MC, MN
93LC66B	2.5-5.5	No	16-bit	I, E	P, SN, ST, MS, OT, MC, MN
93C66A	4.5-5.5	No	8-bit	I, E	P, SN, ST, MS, OT, MC, MN
93C66B	4.5-5.5	No	16-bit	I, E	P, SN, ST, MS, OT, MC, MN
93AA66C	1.8-5.5	Yes	8- or 16-bit	I	P, SN, ST, MS, MC, MN
93LC66C	2.5-5.5	Yes	8- or 16-bit	I, E	P, SN, ST, MS, MC, MN
93C66C	4.5-5.5	Yes	8- or 16-bit	I, E	P, SN, ST, MS, MC, MN

Features:

- Low-Power CMOS Technology
- ORG Pin to Select Word Size for '66C' Version
- 512 x 8-bit Organization 'A' Devices (no ORG)
- 256 x 16-bit organization 'B' Devices (no ORG)
- Self-tImed Erase/Write Cycles (including Auto-Erase)
- Automatic Erase All (ERAL) Before Write All (WRAL)
- Power-On/Off Data Protection Circuitry
- Industry Standard 3-Wire Serial I/O
- Device Status Signal (Ready/$\overline{\text{Busy}}$)
- Sequential Read Function
- 1,000,000 Erase/Write Cycles
- Data Retention > 200 Years
- Pb-free and RoHS Compliant
- Temperature Ranges Supported:
  - Industrial (I)   -40°C to +85°C
  - Automotive (E) -40°C to +125°C
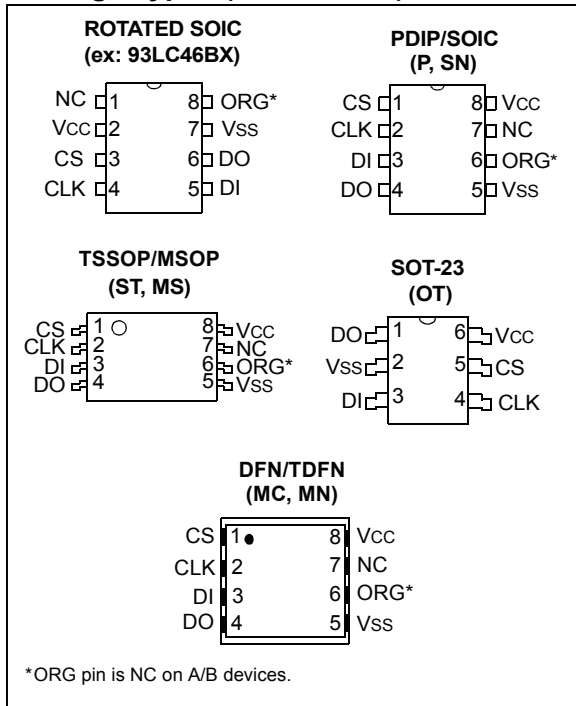
Pin Function Table

Name	Function
CS	Chip Select
CLK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
Vss	Ground
NC	No internal connection
ORG	Memory Configuration
Vcc	Power Supply

Description:

The Microchip Technology Inc. 93XX66A/B/C devices are 4Kbit low-voltage serial Electrically Erasable PROMs (EEPROM). Word-selectable devices such as the 93AA66C, 93LC66C or 93C66C are dependent upon external logic levels driving the ORG pin to set word size. For dedicated 8-bit communication, the 93XX66A devices are available, while the 93XX66B devices provide dedicated 16-bit communication. Advanced CMOS technology makes these devices ideal for low-power, nonvolatile memory applications. The entire 93XX Series is available in standard packages including 8-lead PDIP and SOIC, and advanced packaging including 8-lead MSOP, 6-lead SOT-23, 8-lead 2x3 DFN/TDFN and 8-lead TSSOP. All packages are Pb-free (Matte Tin) finish.

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

Package Types (not to scale)

ROTATED SOIC
(ex: 93LC46BX)

NC	1	8	ORG*
Vcc	2	7	Vss
CS	3	6	DO
CLK	4	5	DI

PDIP/SOIC
(P, SN)

CS	1	8	Vcc
CLK	2	7	NC
DI	3	6	ORG*
DO	4	5	Vss

TSSOP/MSOP
(ST, MS)

CS	1	8	Vcc
CLK	2	7	NC
DI	3	6	ORG*
DO	4	5	Vss

SOT-23
(OT)

DO	1	6	Vcc
Vss	2	5	CS
DI	3	4	CLK

DFN/TDFN
(MC, MN)

CS	1	8	Vcc
CLK	2	7	NC
DI	3	6	ORG*
DO	4	5	Vss

*ORG pin is NC on A/B devices.

1.0   ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings[†]

V_{CC}..7.0V

All inputs and outputs w.r.t. V_{SS} ....-0.6V to V_{CC} +1.0V

Storage temperature ....-65°C to +150°C

Ambient temperature with power applied...-40°C to +125°C

ESD protection on all pins ....≥ 4 kV

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† NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

**TABLE 1-1:   DC CHARACTERISTICS**

All parameters apply over the specified ranges unless otherwise noted.			Industrial (I): T_A = -40°C to +85°C, V_{CC} = +1.8V to +5.5V Automotive (E): T_A = -40°C to +125°C, V_{CC} = +2.5V to +5.5V				
Param. No.	Symbol	Parameter	Min	Typ	Max	Units	Conditions
D1	V_{IH1} V_{IH2}	High-level input voltage	2.0 0.7 V_{CC}	— —	V_{CC} +1 V_{CC} +1	V V	V_{CC} ≥ 2.7V V_{CC} < 2.7V
D2	V_{IL1} V_{IL2}	Low-level input voltage	-0.3 -0.3	— —	0.8 0.2 V_{CC}	V V	V_{CC} ≥ 2.7V V_{CC} < 2.7V
D3	V_{OL1} V_{OL2}	Low-level output voltage	— —	— —	0.4 0.2	V V	I_{OL} = 2.1 mA, V_{CC} = 4.5V I_{OL} = 100 µA, V_{CC} = 2.5V
D4	V_{OH1} V_{OH2}	High-level output voltage	2.4 V_{CC} - 0.2	— —	— —	V V	I_{OH} = -400 µA, V_{CC} = 4.5V I_{OH} = -100 µA, V_{CC} = 2.5V
D5	I_{LI}	Input leakage current	—	—	±1	µA	V_{IN} = V_{SS} or V_{CC}
D6	I_{LO}	Output leakage current	—	—	±1	µA	V_{OUT} = V_{SS} or V_{CC}
D7	C_{IN}, C_{OUT}	Pin capacitance (all inputs/outputs)	—	—	7	pF	V_{IN}/V_{OUT} = 0V **(Note 1)** T_A = 25°C, F_{CLK} = 1 MHz
D8	I_{CC} write	Write current	— —	— 500	2 —	mA µA	F_{CLK} = 3 MHz, V_{CC} = 5.5V F_{CLK} = 2 MHz, V_{CC} = 2.5V
D9	I_{CC} read	Read current	— — —	— — 100	1 500 —	mA µA µA	F_{CLK} = 3 MHz, V_{CC} = 5.5V F_{CLK} = 2 MHz, V_{CC} = 3.0V F_{CLK} = 2 MHz, V_{CC} = 2.5V
D10	I_{CCS}	Standby current	— —	— —	1 5	µA µA	I – Temp E – Temp CLK = Cs = 0V ORG = DI = V_{SS} or V_{CC} **(Note 2) (Note 3)**
D11	V_{POR}	V_{CC} voltage detect 93AA66A/B/C, 93LC66A/B/C 93C66A/B/C	— —	1.5V 3.8V	— —	V V	**(Note 1)**

Note 1:   This parameter is periodically sampled and not 100% tested.

2:   ORG pin not available on 'A' or 'B' versions.

3:   Ready/Busy status must be cleared from DO; see **Section 3.4 "Data Out (DO)"**.

TABLE 1-2: AC CHARACTERISTICS

All parameters apply over the specified ranges unless otherwise noted.			Industrial (I): T_A = -40°C to +85°C, V_{CC} = +1.8V to +5.5V			
			Automotive (E): T_A = -40°C to +125°C, V_{CC} = +2.5V to +5.5V			
Param. No.	Symbol	Parameter	Min	Max	Units	Conditions
A1	F_{CLK}	Clock frequency	—	3	MHz	4.5V $\leq$ V_{CC} < 5.5V, 93XX66C only
				2	MHz	2.5V $\leq$ V_{CC} < 5.5V
				1	MHz	1.8V $\leq$ V_{CC} < 2.5V
A2	T_{CKH}	Clock high time	200	—	ns	4.5V $\leq$ V_{CC} < 5.5V, 93XX66C only
			250		ns	2.5V $\leq$ V_{CC} < 5.5V
			450		ns	1.8V $\leq$ V_{CC} < 2.5V
A3	T_{CKL}	Clock low time	100	—	ns	4.5V $\leq$ V_{CC} < 5.5V, 93XX66C only
			200		ns	2.5V $\leq$ V_{CC} < 5.5V
			450		ns	1.8V $\leq$ V_{CC} < 2.5V
A4	T_{CSS}	Chip Select setup time	50	—	ns	4.5V $\leq$ V_{CC} < 5.5V
			100		ns	2.5V $\leq$ V_{CC} < 4.5V
			250		ns	1.8V $\leq$ V_{CC} < 2.5V
A5	T_{CSH}	Chip Select hold time	0	—	ns	1.8V $\leq$ V_{CC} < 5.5V
A6	T_{CSL}	Chip Select low time	250	—	ns	1.8V $\leq$ V_{CC} < 5.5V
A7	T_{DIS}	Data input setup time	50	—	ns	4.5V $\leq$ V_{CC} < 5.5V, 93XX66C only
			100		ns	2.5V $\leq$ V_{CC} < 5.5V
			250		ns	1.8V $\leq$ V_{CC} < 2.5V
A8	T_{DIH}	Data input hold time	50	—	ns	4.5V $\leq$ V_{CC} < 5.5V, 93XX66C only
			100		ns	2.5V $\leq$ V_{CC} < 5.5V
			250		ns	1.8V $\leq$ V_{CC} < 2.5V
A9	T_{PD}	Data output delay time	—	200	ns	4.5V $\leq$ V_{CC} < 5.5V, CL = 100 pF
				250	ns	2.5V $\leq$ V_{CC} < 4.5V, CL = 100 pF
				400	ns	1.8V $\leq$ V_{CC} < 2.5V, CL = 100 pF
A10	T_{CZ}	Data output disable time	—	100	ns	4.5V $\leq$ V_{CC} < 5.5V, **(Note 1)**
				200	ns	1.8V $\leq$ V_{CC} < 4.5V, **(Note 1)**
A11	T_{SV}	Status valid time	—	200	ns	4.5V $\leq$ V_{CC} < 5.5V, CL = 100 pF
				300	ns	2.5V $\leq$ V_{CC} < 4.5V, CL = 100 pF
				500	ns	1.8V $\leq$ V_{CC} < 2.5V, CL = 100 pF
A12	T_{WC}	Program cycle time	—	6	ms	Erase/Write mode (AA and LC versions)
A13	T_{WC}		—	2	ms	Erase/Write mode (93C versions)
A14	T_{EC}		—	6	ms	ERAL mode, 4.5V $\leq$ V_{CC} $\leq$ 5.5V
A15	T_{WL}		—	15	ms	WRAL mode, 4.5V $\leq$ V_{CC} $\leq$ 5.5V
A16	—	Endurance	1M	—	cycles	25°C, V_{CC} = 5.0V, **(Note 2)**

Note 1: This parameter is periodically sampled and not 100% tested.

2: This application is not tested but ensured by characterization. For endurance estimates in a specific application, please consult the Total Endurance™ Model, which may be obtained from Microchip's web site at www.microchip.com.

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

FIGURE 1-1: SYNCHRONOUS DATA TIMING

Note: T$_{SV}$ is relative to CS.
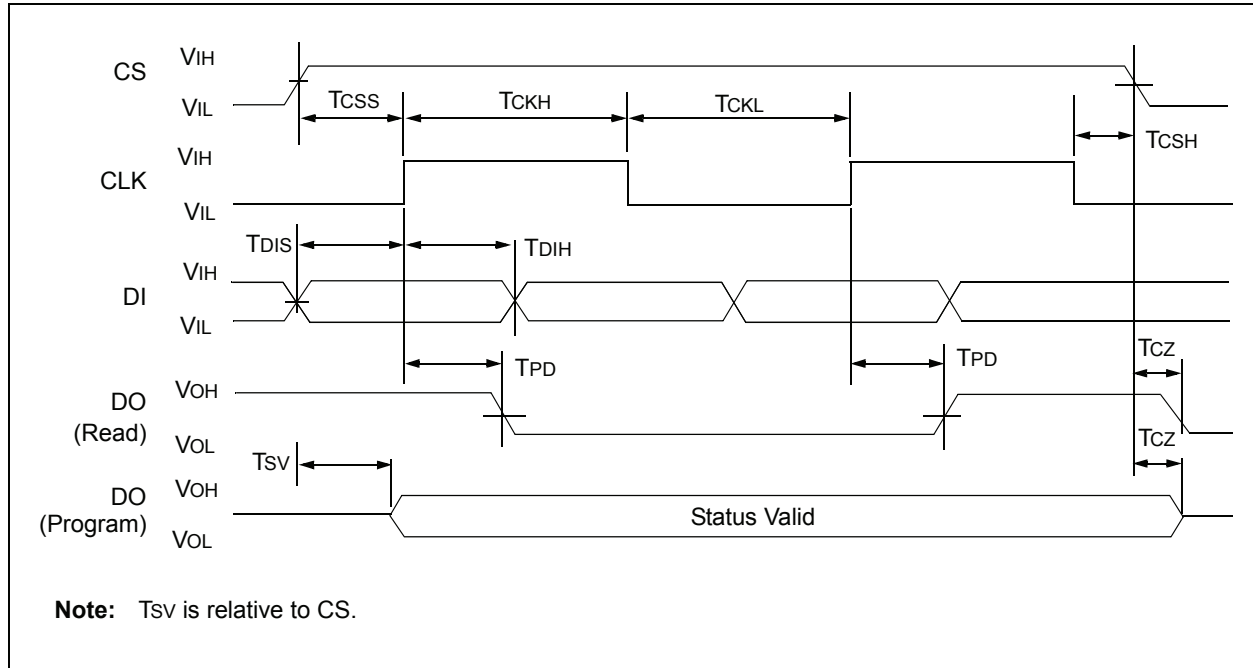
TABLE 1-3: INSTRUCTION SET FOR X16 ORGANIZATION (93XX66B OR 93XX66C WITH ORG = 1)

Instruction	SB	Opcode	Address								Data In	Data Out	Req. CLK Cycles
ERASE	1	11	A7	A6	A5	A4	A3	A2	A1	A0	—	(RDY/$\overline{BSY}$)	11
ERAL	1	00	1	0	X	X	X	X	X	X	—	(RDY/$\overline{BSY}$)	11
EWDS	1	00	0	0	X	X	X	X	X	X	—	High-Z	11
EWEN	1	00	1	1	X	X	X	X	X	X	—	High-Z	11
READ	1	10	A7	A6	A5	A4	A3	A2	A1	A0	—	D15 – D0	27
WRITE	1	01	A7	A6	A5	A4	A3	A2	A1	A0	D15 – D0	(RDY/$\overline{BSY}$)	27
WRAL	1	00	0	1	X	X	X	X	X	X	D15 – D0	(RDY/$\overline{BSY}$)	27

TABLE 1-4: INSTRUCTION SET FOR X8 ORGANIZATION (93XX66A OR 93XX66C WITH ORG = 0)

Instruction	SB	Opcode	Address									Data In	Data Out	Req. CLK Cycles
ERASE	1	11	A8	A7	A6	A5	A4	A3	A2	A1	A0	—	(RDY/$\overline{BSY}$)	12
ERAL	1	00	1	0	X	X	X	X	X	X	X	—	(RDY/$\overline{BSY}$)	12
EWDS	1	00	0	0	X	X	X	X	X	X	X	—	High-Z	12
EWEN	1	00	1	1	X	X	X	X	X	X	X	—	High-Z	12
READ	1	10	A8	A7	A6	A5	A4	A3	A2	A1	A0	—	D7 – D0	20
WRITE	1	01	A8	A7	A6	A5	A4	A3	A2	A1	A0	D7 – D0	(RDY/$\overline{BSY}$)	20
WRAL	1	00	0	1	X	X	X	X	X	X	X	D7 – D0	(RDY/$\overline{BSY}$)	20

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

2.0 FUNCTIONAL DESCRIPTION

When the ORG pin is connected to Vcc, the (x16) organization is selected. When it is connected to ground, the (x8) organization is selected. Instructions, addresses and write data are clocked into the DI pin on the rising edge of the clock (CLK). The DO pin is normally held in a High-Z state except when reading data from the device, or when checking the Ready/Busy status during a programming operation. The Ready/Busy status can be verified during an Erase/Write operation by polling the DO pin; DO low indicates that programming is still in progress, while DO high indicates the device is ready. DO will enter the High-Z state on the falling edge of CS.

2.1 Start Condition

The Start bit is detected by the device if CS and DI are both high with respect to the positive edge of CLK for the first time.

Before a Start condition is detected, CS, CLK and DI may change in any combination (except to that of a Start condition), without resulting in any device operation (Read, Write, Erase, EWEN, EWDS, ERAL or WRAL). As soon as CS is high, the device is no longer in Standby mode.

An instruction following a Start condition will only be executed if the required opcode, address and data bits for any particular instruction are clocked in.

Note:	When preparing to transmit an instruction, either the CLK or DI signal levels must be at a logic low as CS is toggled active high.

2.2 Data In/Data Out (DI/DO)

It is possible to connect the Data In and Data Out pins together. However, with this configuration it is possible for a "bus conflict" to occur during the "dummy zero" that precedes the read operation, if A0 is a logic high level. Under such a condition the voltage level seen at Data Out is undefined and will depend upon the relative impedances of Data Out and the signal source driving A0. The higher the current sourcing capability of A0, the higher the voltage at the Data Out pin. In order to limit this current, a resistor should be connected between DI and DO.

2.3 Data Protection

All modes of operation are inhibited when Vcc is below a typical voltage of 1.5V for '93AA' and '93LC' devices or 3.8V for '93C' devices.

The EWEN and EWDS commands give additional protection against accidentally programming during normal operation.

Note:	For added protection, an EWDS command should be performed after every write operation.

After power-up, the device is automatically in the EWDS mode. Therefore, an EWEN instruction must be performed before the initial ERASE or WRITE instruction can be executed.

Block Diagram

*ORG input is not available on A/B devices
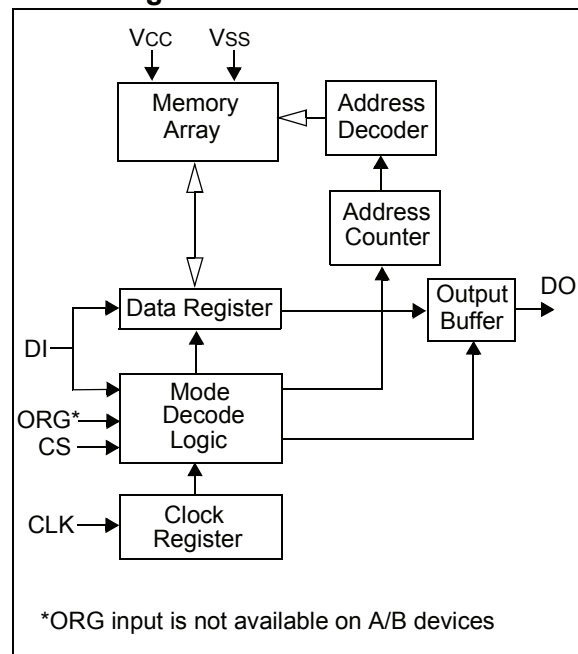
2.4 Erase

The ERASE instruction forces all data bits of the specified address to the logical '1' state. CS is brought low following the loading of the last address bit. This falling edge of the CS pin initiates the self-timed programming cycle, except on '93C' devices where the rising edge of CLK before the last address bit initiates the write cycle.
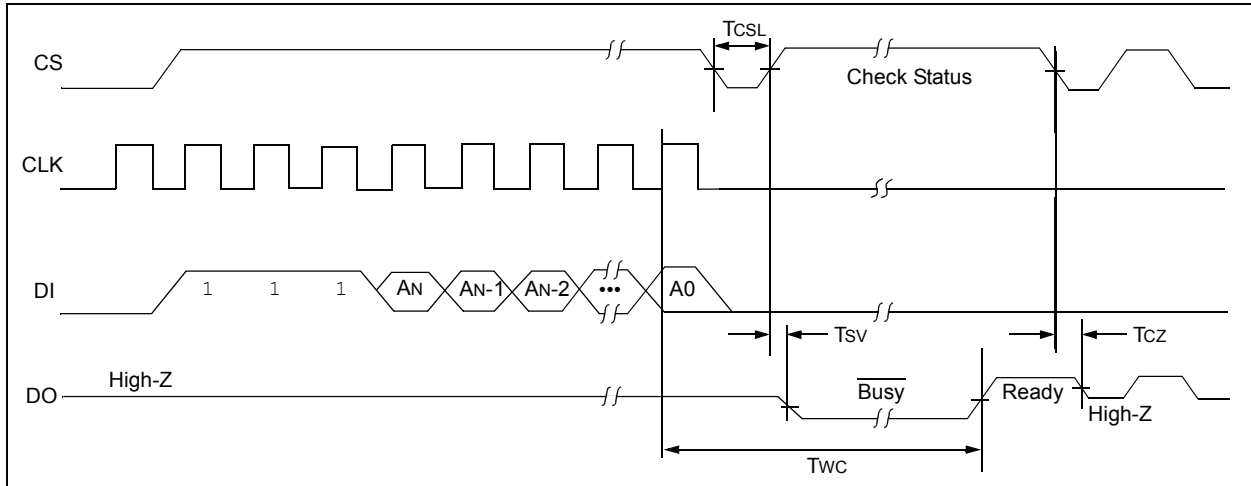
The DO pin indicates the Ready/$\overline{\text{Busy}}$ status of the device if CS is brought high after a minimum of 250 ns low (T_{CSL}). DO at logical '0' indicates that programming is still in progress. DO at logical '1' indicates that the register at the specified address has been erased and the device is ready for another instruction.

Note: Issuing a Start bit and then taking CS low will clear the Ready/$\overline{\text{Busy}}$ status from DO.

FIGURE 2-1: ERASE TIMING FOR 93AA AND 93LC DEVICES
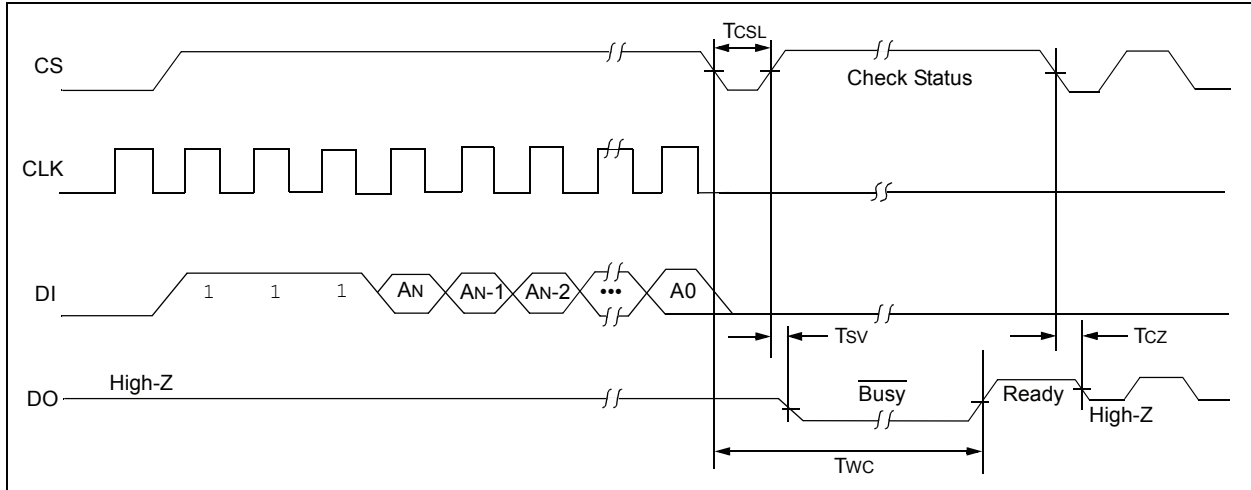
FIGURE 2-2: ERASE TIMING FOR 93C DEVICES

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

2.5   Erase All (ERAL)

The Erase All (ERAL) instruction will erase the entire memory array to the logical '1' state. The ERAL cycle is identical to the erase cycle, except for the different opcode. The ERAL cycle is completely self-timed and commences at the falling edge of the CS, except on '93C' devices where the rising edge of CLK before the last data bit initiates the write cycle. Clocking of the CLK pin is not necessary after the device has entered the ERAL cycle.

The DO pin indicates the Ready/$\overline{\text{Busy}}$ status of the device, if CS is brought high after a minimum of 250 ns low (T$_{CSL}$).

Note: Issuing a Start bit and then taking CS low will clear the Ready/$\overline{\text{Busy}}$ status from DO.

V$_{CC}$ must be $\geq$ 4.5V for proper operation of ERAL.

FIGURE 2-3:   **ERAL TIMING FOR 93AA AND 93LC DEVICES**

V$_{CC}$ must be $\geq$4.5V for proper operation of ERAL.
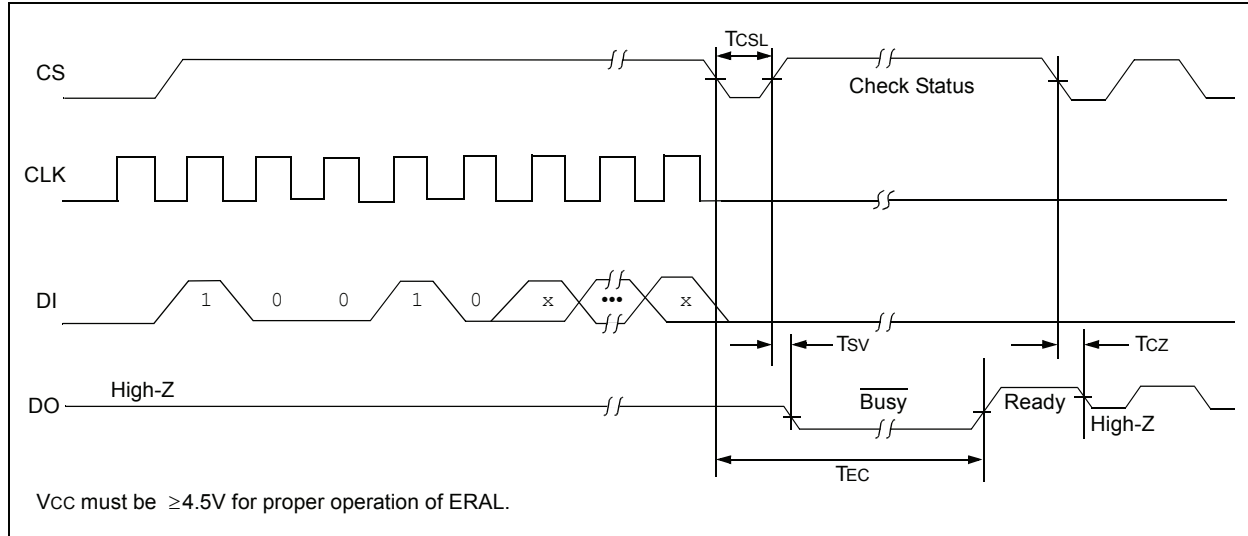
FIGURE 2-4:   **ERAL TIMING FOR 93C DEVICES**
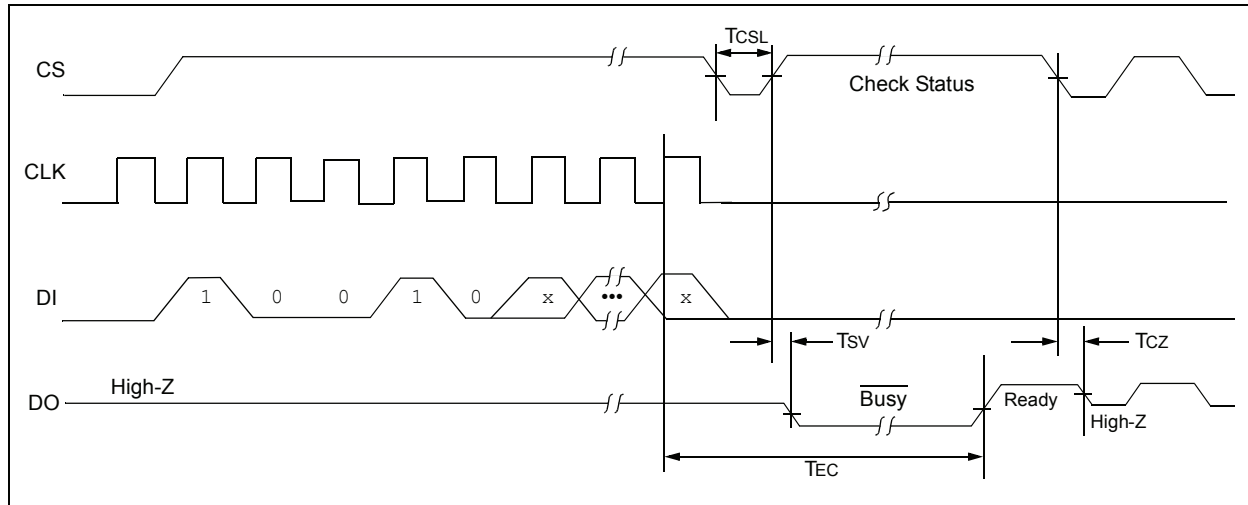
2.6 Erase/Write Disable and Enable (EWDS/EWEN)

The 93XX66A/B/C powers up in the Erase/Write Disable (EWDS) state. All Programming modes must be preceded by an Erase/Write Enable (EWEN) instruction. Once the EWEN instruction is executed, programming remains enabled until an EWDS instruction is executed or Vcc is removed from the device.

To protect against accidental data disturbance, the EWDS instruction can be used to disable all erase/write functions and should follow all programming operations. Execution of a READ instruction is independent of both the EWEN and EWDS instructions.

FIGURE 2-5: **EWDS TIMING**
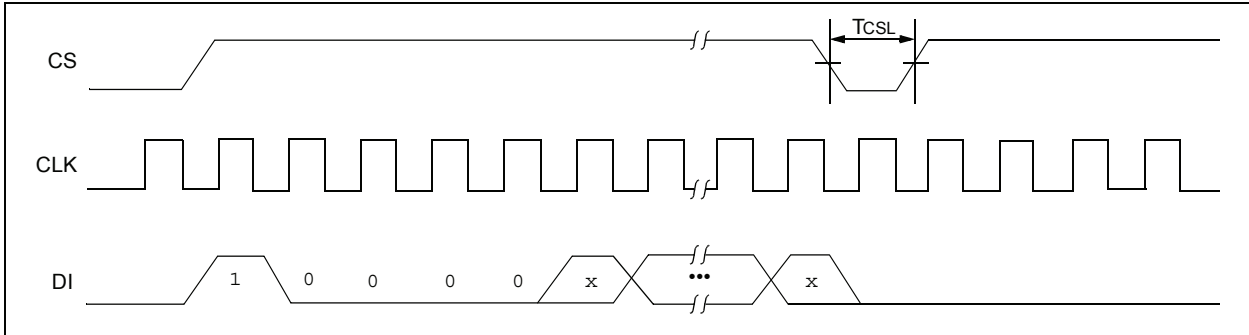
FIGURE 2-6: **EWEN TIMING**
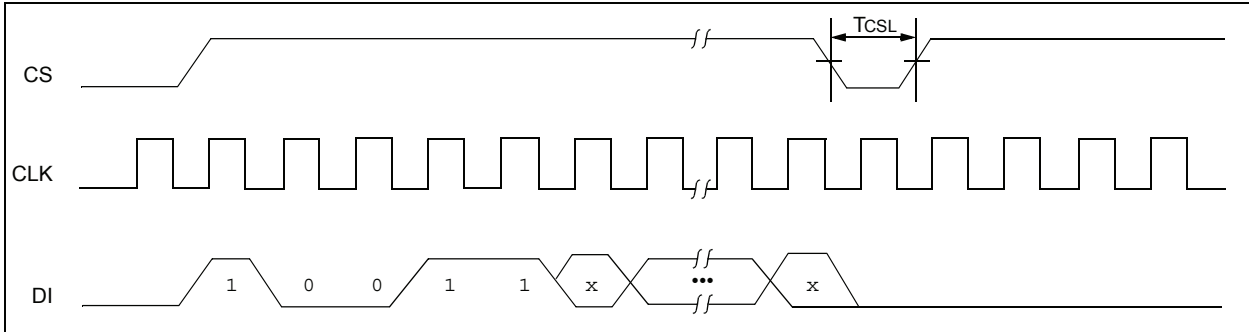
2.7 Read

The READ instruction outputs the serial data of the addressed memory location on the DO pin. A dummy zero bit precedes the 8-bit (If ORG pin is low or A-Version devices) or 16-bit (If ORG pin is high or B-version devices) output string. The output data bits will toggle on the rising edge of the CLK and are stable after the specified time delay (TPD). Sequential read is possible when CS is held high. The memory data will automatically cycle to the next register and output sequentially.

FIGURE 2-7: **READ TIMING**
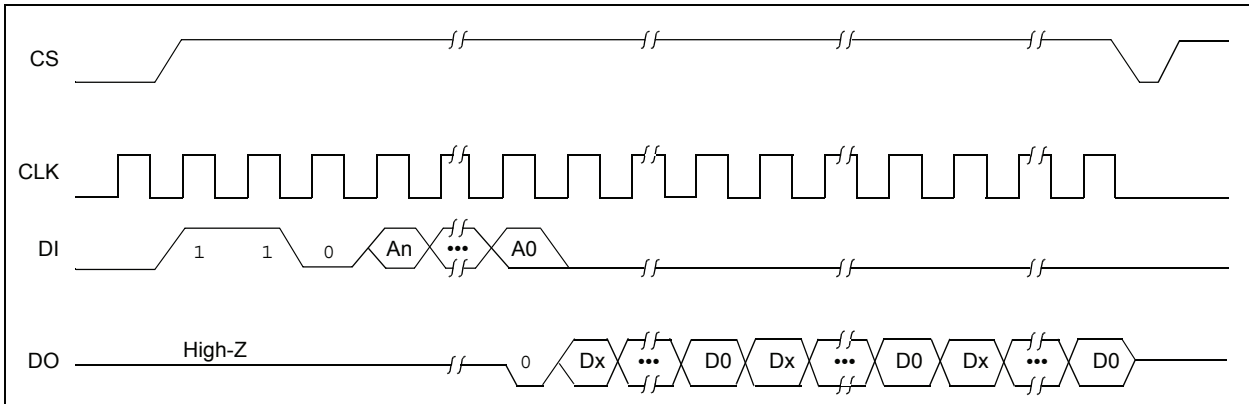
93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

2.8   Write

The `WRITE` instruction is followed by 8 bits (If ORG is low or A-version devices) or 16 bits (If ORG pin is high or B-version devices) of data which are written into the specified address. For 93AA66A/B/C and 93LC66A/B/C devices, after the last data bit is clocked into DI, the falling edge of CS initiates the self-timed auto-erase and programming cycle. For 93C66A/B/C devices, the self-timed auto-erase and programming cycle is initiated by the rising edge of CLK on the last data bit.

The DO pin indicates the Ready/$\overline{\text{Busy}}$ status of the device, if CS is brought high after a minimum of 250 ns low (TCSL). DO at logical '0' indicates that programming is still in progress. DO at logical '1' indicates that the register at the specified address has been written with the data specified and the device is ready for another instruction.

Note: Issuing a Start bit and then taking CS low will clear the Ready/$\overline{\text{Busy}}$ status from DO.

FIGURE 2-8:   WRITE TIMING FOR 93AA AND 93LC DEVICES
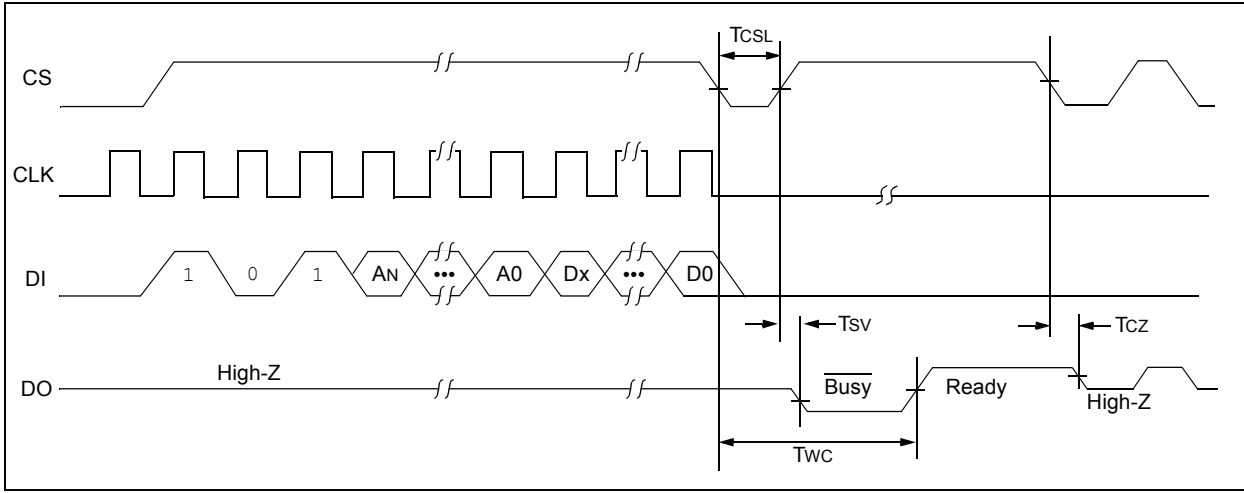
FIGURE 2-9:   WRITE TIMING FOR 93C DEVICES
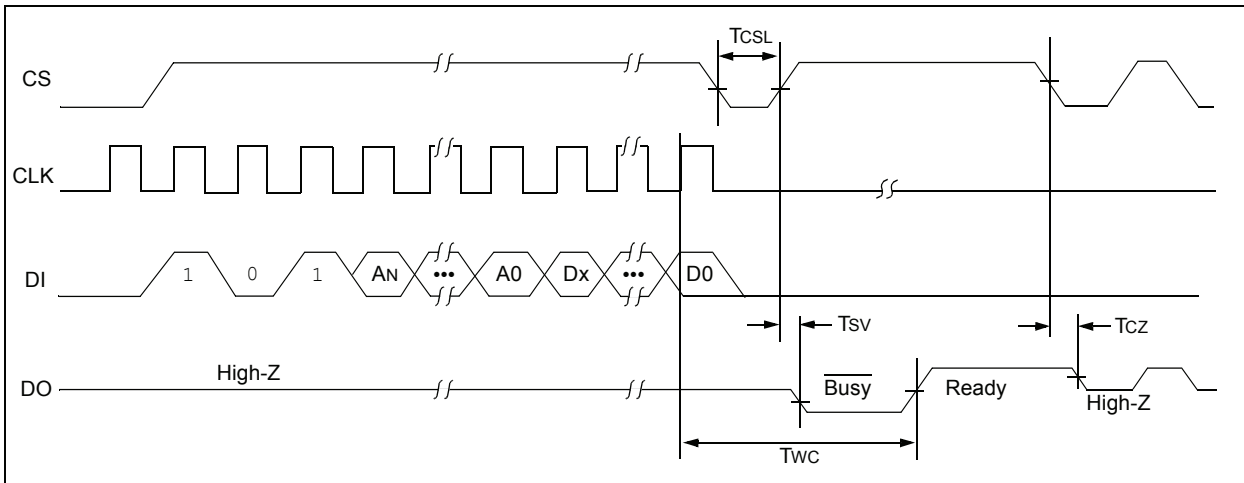
2.9   Write All (WRAL)

The Write All (WRAL) instruction will write the entire memory array with the data specified in the command. For 93AA66A/B/C and 93LC66A/B/C devices, after the last data bit is clocked into DI, the falling edge of CS initiates the self-timed auto-erase and programming cycle. For 93C66A/B/C devices, the self-timed auto-erase and programming cycle is initiated by the rising edge of CLK on the last data bit. Clocking of the CLK pin is not necessary after the device has entered the WRAL cycle. The WRAL command does include an automatic ERAL cycle for the device. Therefore, the WRAL instruction does not require an ERAL instruction, but the chip must be in the EWEN status.

The DO pin indicates the Ready/$\overline{\text{Busy}}$ status of the device if CS is brought high after a minimum of 250 ns low (T$_{CSL}$).

Note: Issuing a Start bit and then taking CS low will clear the Ready/$\overline{\text{Busy}}$ status from DO.

V$_{CC}$ must be ≥ 4.5V for proper operation of WRAL.

FIGURE 2-10:   WRAL TIMING FOR 93AA AND 93LC DEVICES

V$_{CC}$ must be ≥4.5V for proper operation of WRAL.
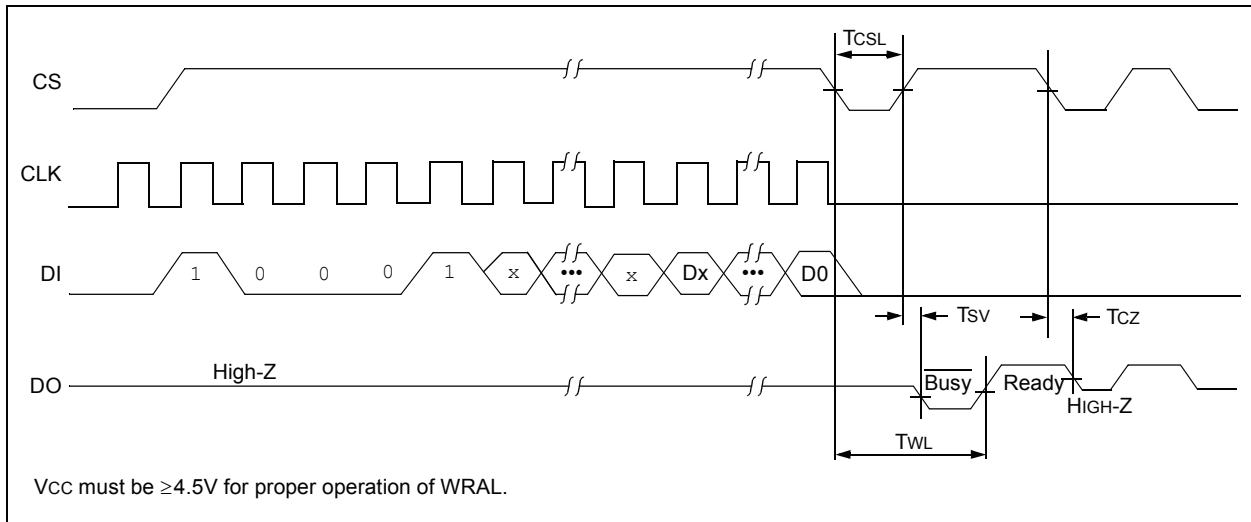
FIGURE 2-11:   WRAL TIMING FOR 93C DEVICES
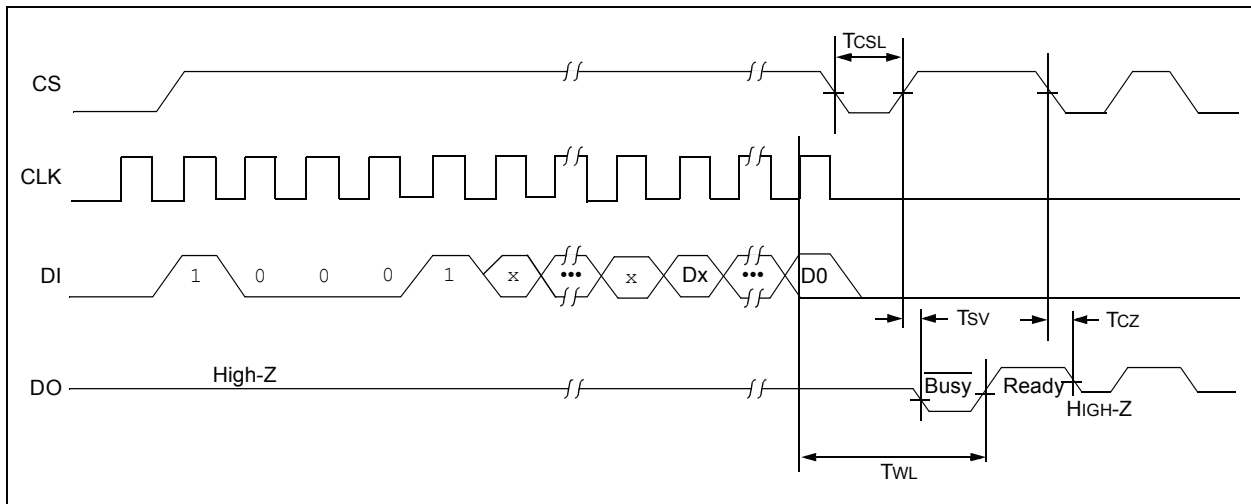
93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

3.0 PIN DESCRIPTIONS

TABLE 3-1: PIN DESCRIPTIONS

Name	PDIP	SOIC	TSSOP	MSOP	DFN[1]	TDFN[1]	SOT-23	Rotated SOIC	Function
CS	1	1	1	1	1	1	5	3	Chip Select
CLK	2	2	2	2	2	2	4	4	Serial Clock
DI	3	3	3	3	3	3	3	5	Data In
DO	4	4	4	4	4	4	1	6	Data Out
V_{SS}	5	5	5	5	5	5	2	7	Ground
ORG/NC	6	6	6	6	6	6	N/A	8	Organization / 93XX66C No Internal Connection / 93XX66A/B
NC	7	7	7	7	7	7	N/A	1	No Internal Connection
V_{CC}	8	8	8	8	8	8	6	2	Power Supply

Note 1: The exposed pad on the DFN/TDFN package may be connected to V_{SS} or left floating.

3.1 Chip Select (CS)

A high level selects the device; a low level deselects the device and forces it into Standby mode. However, a programming cycle which is already in progress will be completed, regardless of the Chip Select (CS) input signal. If CS is brought low during a program cycle, the device will go into Standby mode as soon as the programming cycle is completed.

CS must be low for 250 ns minimum (T_{CSL}) between consecutive instructions. If CS is low, the internal control logic is held in a Reset status.

3.2 Serial Clock (CLK)

The Serial Clock is used to synchronize the communication between a master device and the 93XX series device. Opcodes, address and data bits are clocked in on the positive edge of CLK. Data bits are also clocked out on the positive edge of CLK.

CLK can be stopped anywhere in the transmission sequence (at high or low level) and can be continued anytime with respect to Clock High Time (T_{CKH}) and Clock Low Time (T_{CKL}). This gives the controlling master freedom in preparing opcode, address and data.

CLK is a "don't care" if CS is low (device deselected). If CS is high, but the Start condition has not been detected (DI = 0), any number of clock cycles can be received by the device without changing its status (i.e., waiting for a Start condition).

CLK cycles are not required during the self-timed write (i.e., auto erase/write) cycle.

After detection of a Start condition the specified number of clock cycles (respectively low-to-high transitions of CLK) must be provided. These clock cycles are required to clock in all required opcode, address and data bits before an instruction is executed. CLK and DI then become "don't care" inputs waiting for a new Start condition to be detected.

3.3 Data In (DI)

Data In (DI) is used to clock in a Start bit, opcode, address and data synchronously with the CLK input.

3.4 Data Out (DO)

Data Out (DO) is used in the Read mode to output data synchronously with the CLK input (T_{PD} after the positive edge of CLK).

This pin also provides Ready/$\overline{Busy}$ status information during erase and write cycles. Ready/$\overline{Busy}$ status information is available on the DO pin if CS is brought high after being low for minimum Chip Select Low Time (T_{CSL}) and an erase or write operation has been initiated.

The Status signal is not available on DO, if CS is held low during the entire erase or write cycle. In this case, DO is in the High-Z mode. If status is checked after the erase/write cycle, the data line will be high to indicate the device is ready.

Note: Issuing a Start bit and then taking CS low will clear the Ready/$\overline{Busy}$ status from DO.

3.5 Organization (ORG)

When the ORG pin is connected to V_{CC} or Logic HI, the (x16) memory organization is selected. When the ORG pin is tied to V_{SS} or Logic LO, the (x8) memory organization is selected. For proper operation, ORG must be tied to a valid logic level.
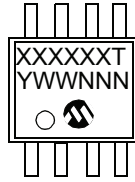
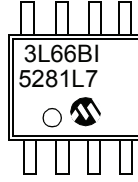93XX66A devices are always (x8) organization and 93XX66B devices are always (x16) organization.

4.0 PACKAGING INFORMATION

4.1 Package Marking Information

8-Lead MSOP (150 mil)

Example:

```
XXXXXXXT
YWWNNN
  ○  Ⓜ
```

```
3L66BI
5281L7
  ○  Ⓜ
```
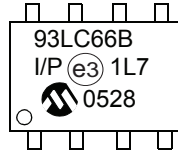
6-Lead SOT-23

Example:

```
XXNN
○
```

```
3EL7
○
```

8-Lead PDIP

Example:

```
XXXXXXXX
T/XXXNNN
○  Ⓜ YYWW
```

```
93LC66B
I/P Ⓔ3 1L7
○  Ⓜ 0528
```

8-Lead SOIC

Example:

```
XXXXXXXT
XXXXYYWW
○  Ⓜ  NNN
```

```
93LC66BI
SN Ⓔ3 0528
○  Ⓜ  1L7
```

8-Lead TSSOP

Example:

```
○ XXXX
  TYWW
Ⓜ NNN
```

```
○ L66B
  I528
Ⓜ 1L7
```
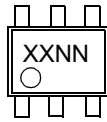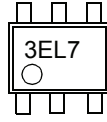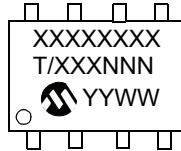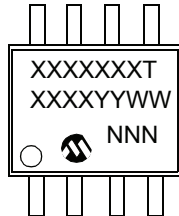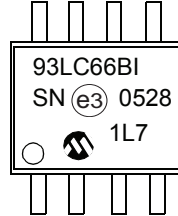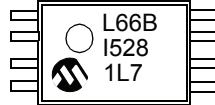
8-Lead 2x3 DFN

Example:

```
 XXX
 YWW
● NN
```

```
 374
 528
● L7
```
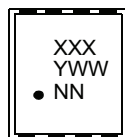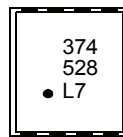
8-Lead 2x3 TDFN

Example:

```
 XXX
 YWW
● NN
```

```
 E74
 528
● L7
```
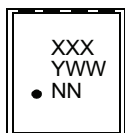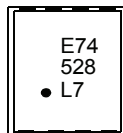
93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

Part Number	1st Line Marking Codes							
	TSSOP	MSOP	SOT-23		DFN		TDFN	
			I Temp.	E Temp.	I Temp.	E Temp.	I Temp.	E Temp.
93AA66A	A66A	3A66AT	3BNN	—	361	—	E61	—
93AA66B	A66B	3A66BT	3LNN	—	371	—	E71	—
93AA66C	A66C	3A66CT	—	—	381	—	E81	—
93LC66A	L66A	3L66AT	3ENN	3FNN	364	—	E64	E65
93LC66B	L66B	3L66BT	3PNN	3RNN	374	—	E74	E75
93LC66C	L66C	3L66CT	—	—	384	—	E84	E85
93C66A	C66A	3C66AT	3HNN	3JNN	367	—	E67	E68
93C66B	C66B	3C66BT	3TNN	3UNN	377	—	E77	E78
93C66C	C66C	3C66CT	—	—	387	—	E87	E88

Note: T = Temperature grade (I, E)
NN = Alphanumeric traceability code

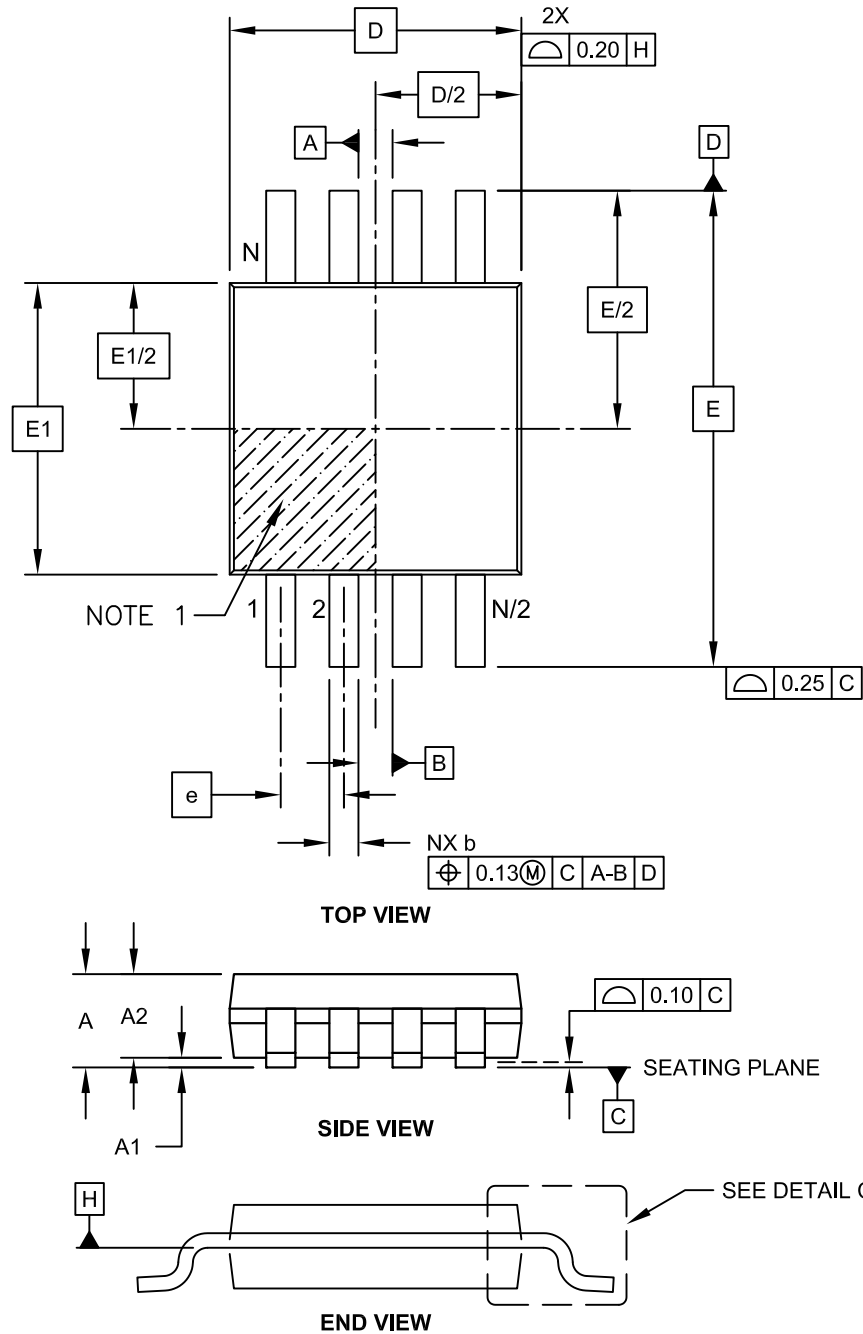| Legend:	XX...X	Part number or part number code
	T	Temperature (I, E)
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code (2 characters for small packages)
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)

Note: For very small packages with no room for the Pb-free JEDEC designator (e3), the marking will only appear on the outer carton or reel label.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

TOP VIEW

SIDE VIEW

END VIEW

Microchip Technology Drawing C04-111C Sheet 1 of 2

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

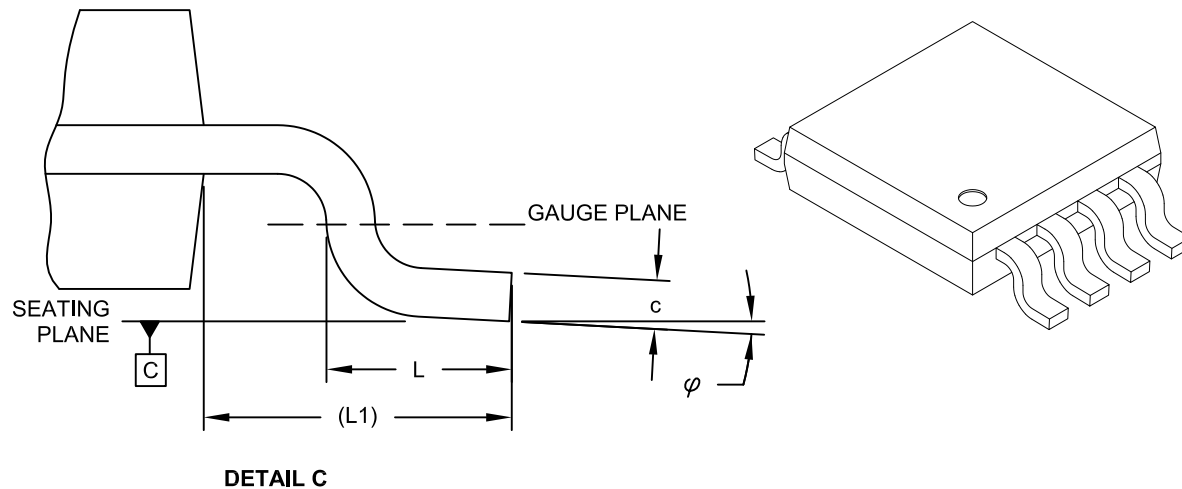| Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

SEATING PLANE

C

GAUGE PLANE

c

φ

L

(L1)

DETAIL C

	Units		MILLIMETERS	
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		0.65 BSC	
Overall Height	A	-	-	1.10
Molded Package Thickness	A2	0.75	0.85	0.95
Standoff	A1	0.00	-	0.15
Overall Width	E		4.90 BSC	
Molded Package Width	E1		3.00 BSC	
Overall Length	D		3.00 BSC	
Foot Length	L	0.40	0.60	0.80
Footprint	L1		0.95 REF	
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.08	-	0.23
Lead Width	b	0.22	-	0.40

Notes:
1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
3. Dimensioning and tolerancing per ASME Y14.5M.
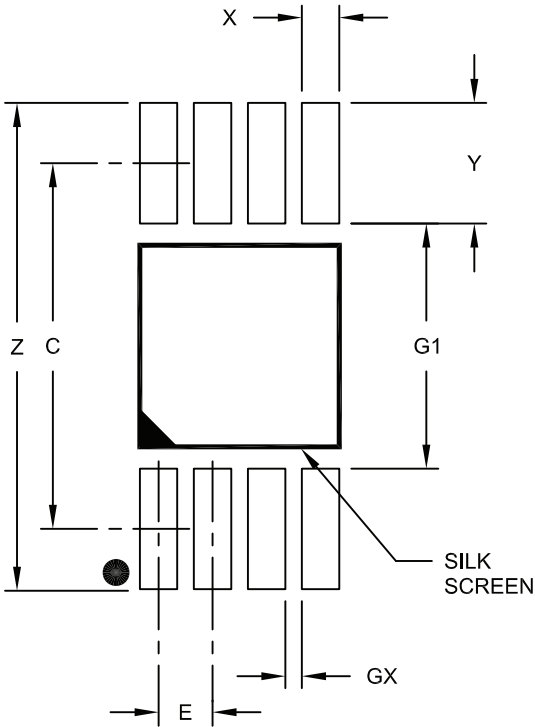   BSC: Basic Dimension. Theoretically exact value shown without tolerances.
    REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging		

RECOMMENDED LAND PATTERN

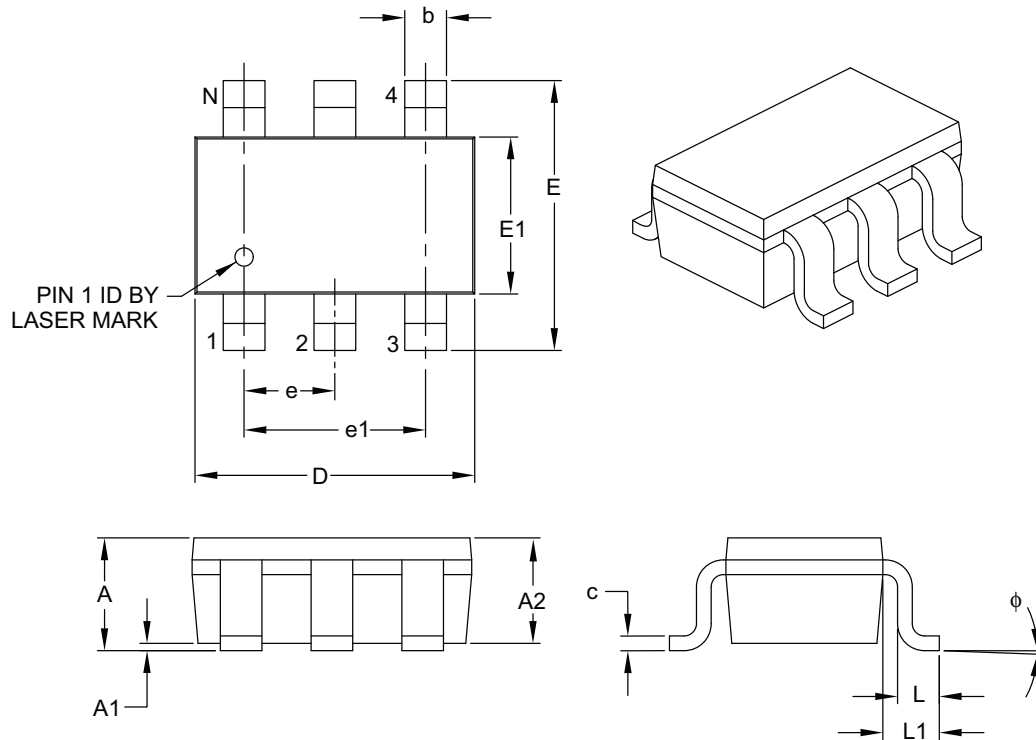|	Units	MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	C		4.40	
Overall Width	Z			5.85
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G1	2.95		
Distance Between Pads	GX	0.20		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

6-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		6	
Pitch	e		0.95 BSC	
Outside Lead Pitch	e1		1.90 BSC	
Overall Height	A	0.90	–	1.45
Molded Package Thickness	A2	0.89	–	1.30
Standoff	A1	0.00	–	0.15
Overall Width	E	2.20	–	3.20
Molded Package Width	E1	1.30	–	1.80
Overall Length	D	2.70	–	3.10
Foot Length	L	0.10	–	0.60
Footprint	L1	0.35	–	0.80
Foot Angle	φ	0°	–	30°
Lead Thickness	c	0.08	–	0.26
Lead Width	b	0.20	–	0.51

Notes:
1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
2. Dimensioning and tolerancing per ASME Y14.5M.
   BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-028B

6-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN
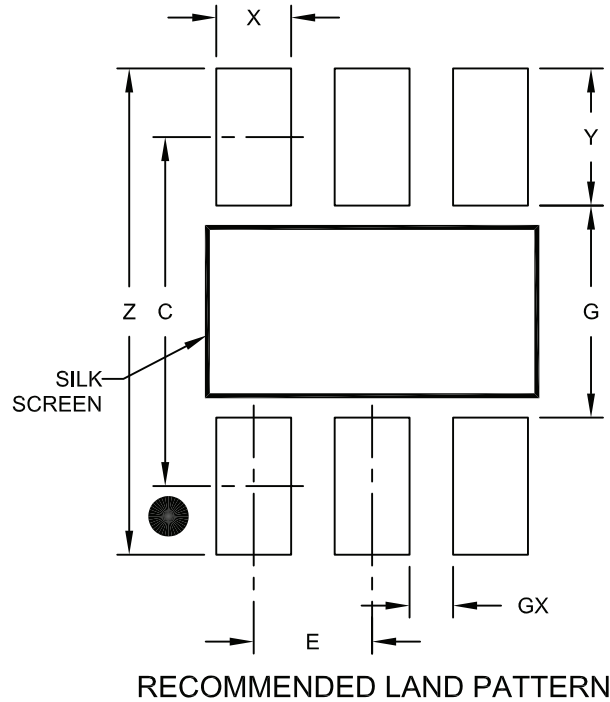
	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		0.95 BSC	
Contact Pad Spacing	C		2.80	
Contact Pad Width (X6)	X			0.60
Contact Pad Length (X6)	Y			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Z			3.90

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2028A

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

8-Lead Plastic Dual In-Line (P) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging
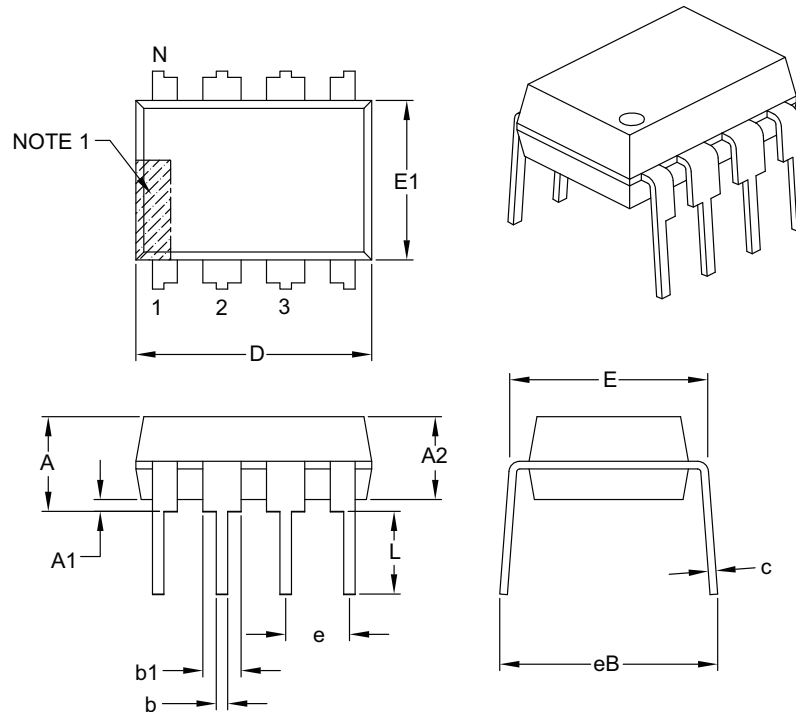
|	Units		INCHES	
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		.100 BSC	
Top to Seating Plane	A	–	–	.210
Molded Package Thickness	A2	.115	.130	.195
Base to Seating Plane	A1	.015	–	–
Shoulder to Shoulder Width	E	.290	.310	.325
Molded Package Width	E1	.240	.250	.280
Overall Length	D	.348	.365	.400
Tip to Seating Plane	L	.115	.130	.150
Lead Thickness	c	.008	.010	.015
Upper Lead Width	b1	.040	.060	.070
Lower Lead Width	b	.014	.018	.022
Overall Row Spacing §	eB	–	–	.430

Notes:
1. Pin 1 visual index feature may vary, but must be located with the hatched area.
2. § Significant Characteristic.
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
4. Dimensioning and tolerancing per ASME Y14.5M.
   BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-018B

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

TOP VIEW

SIDE VIEW

VIEW A-A
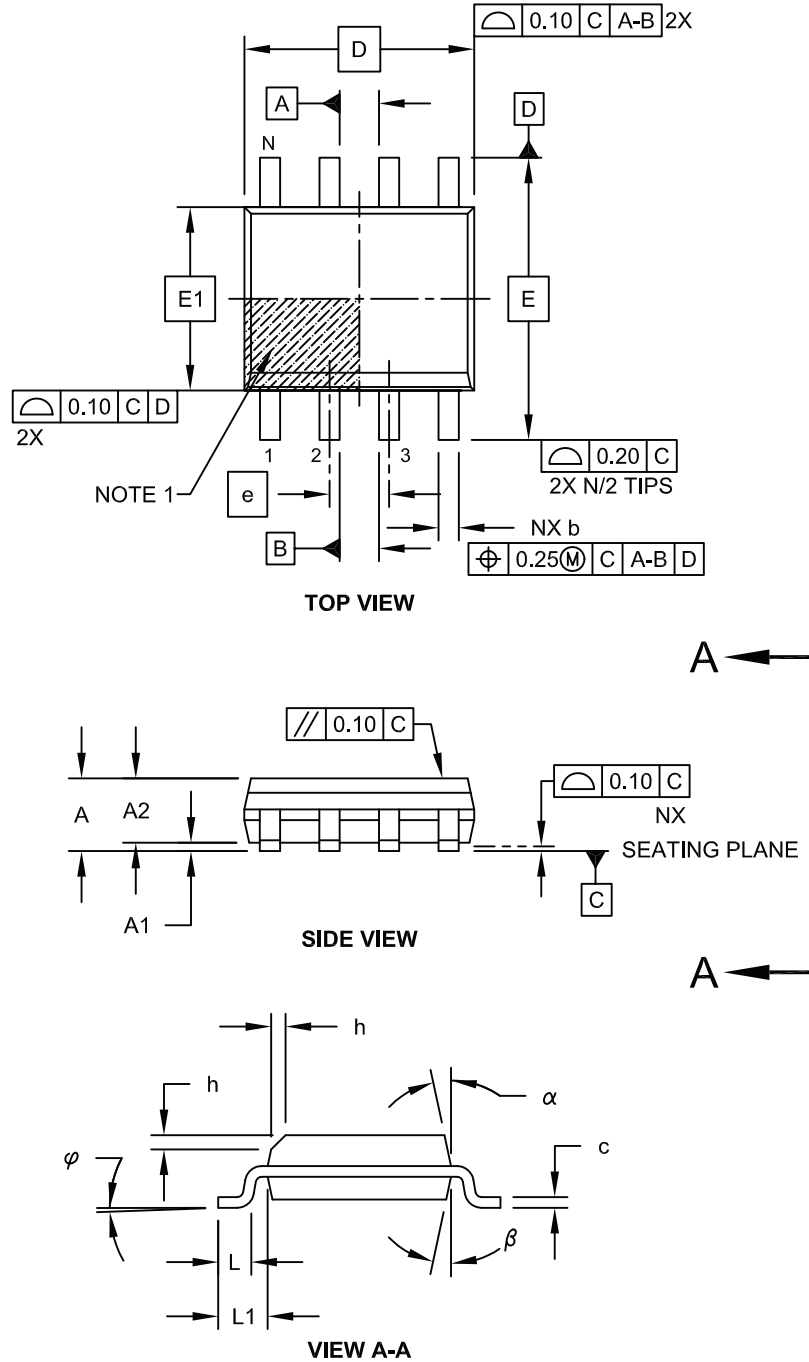
Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

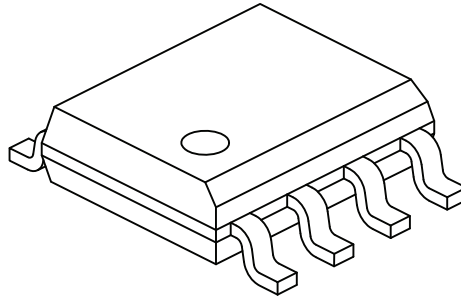| Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		1.27 BSC	
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E		6.00 BSC	
Molded Package Width	E1		3.90 BSC	
Overall Length	D		4.90 BSC	
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1		1.04 REF	
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.17	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M

      BSC: Basic Dimension. Theoretically exact value shown without tolerances.
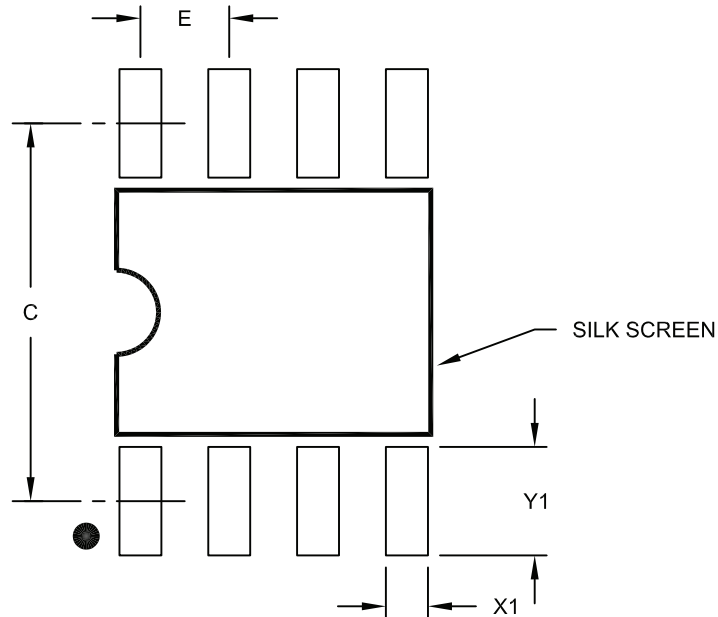   REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

	Units	MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

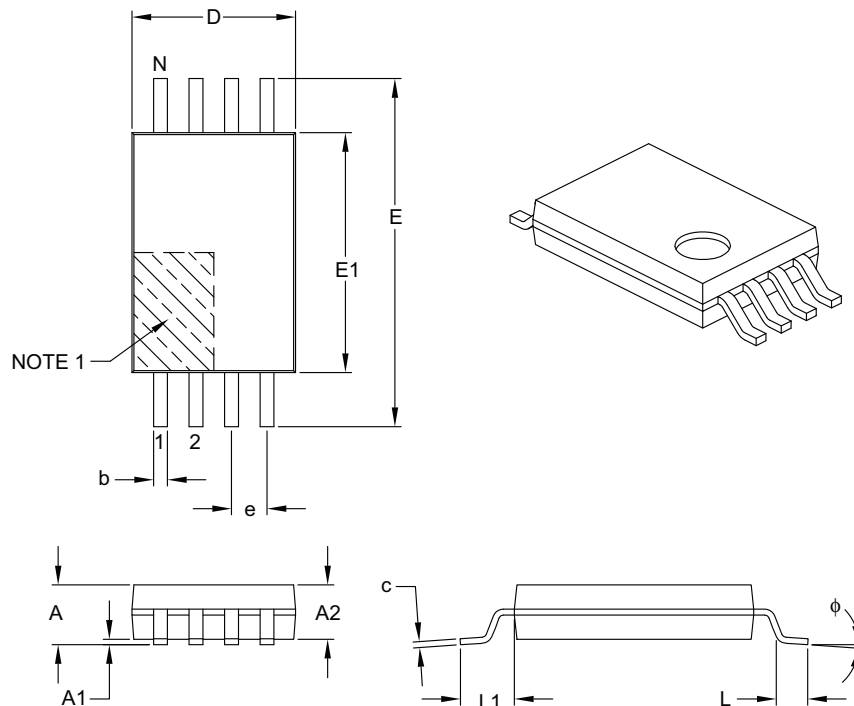   BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

93AA66A/B/C, 93LC66A/B/C, 93C66A/B/C

8-Lead Plastic Thin Shrink Small Outline (ST) – 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	Units		MILLIMETERS	
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		0.65 BSC	
Overall Height	A	–	–	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	–	0.15
Overall Width	E		6.40 BSC	
Molded Package Width	E1	4.30	4.40	4.50
Molded Package Length	D	2.90	3.00	3.10
Foot Length	L	0.45	0.60	0.75
Footprint	L1		1.00 REF	
Foot Angle	φ	0°	–	8°
Lead Thickness	c	0.09	–	0.20
Lead Width	b	0.19	–	0.30

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.

3. Dimensioning and tolerancing per ASME Y14.5M.

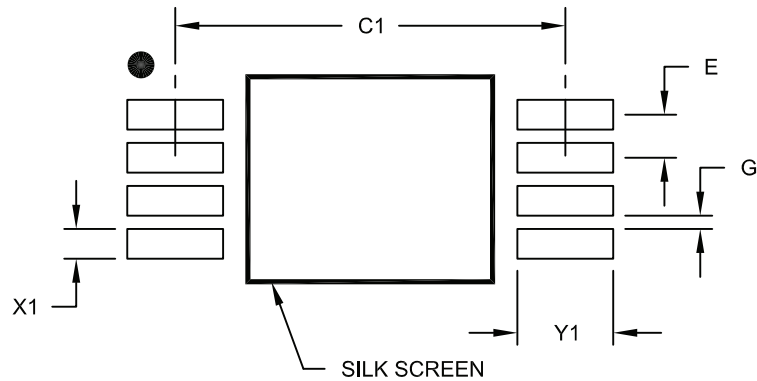   BSC: Basic Dimension. Theoretically exact value shown without tolerances.
    REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-086B

8-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	C1		5.90	
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G	0.20		

Notes:
1. Dimensioning and tolerancing per ASME Y14.5M
   BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2086A